Call for Papers

3 Steps to Contribute a Presentation

Join JSAP

Regular Membership
Admission Fee: 10,000 JPY
Annual Due*: 10,000 JPY
*Annual due will be waived for the first year.

Graduate Student/ Student Membership
Admission Fee: 3,000JPY
Annual Due*: 3,000 JPY
*Annual due will be waived for the first year.

Submit

Submission Deadline:
June 27 (Tue.), 2017 (17:00, JST)

No late submission is accepted after the deadline.

Online submission will open in mid May.

Register

Registration Deadline:
August 16 (Wed.), 2017

***The conference registration fees has been revised.**
Advanced
JSAP Official Member / Partner Society Member: 12,000 JPY
JSAP Senior Member: 4,000 JPY
Student: 3,000 JPY
Non-member: 23,000 JPY

Onsite
JSAP Official Member /
JSAP Senior Member: 7,000 JPY
Student : 5,000 JPY
Partner Society Member: 18,000 JPY
Non-member: 30,000 JPY

Online pre-registration open in mid May.

Submission Deadline

June 27 (Tue.), 2017 (5:00pm, JST)

*No late submission is accepted.

Call for Papers

Papers are solicited for the following sessions (table 1-3);

The date and section of your presentation will be determined by our program committee held on July 3 and informed you in late July. Your papers may be forwarded from a regular session to a symposium and vice versa.

Table 1. Regular Sessions

Category	Section	
1 Interdisciplinary Physics and Related Areas of Science and Technology	1.1	Interdisciplinary and general physics
	1.2	Education
	1.3	Novel technologies and interdisciplinary engineering
	1.4	Energy conversion and storage, resources and environment
	1.5	Instrumentation, measurement and metrology
	1.6	Ultrasonics
2 Ionizing Radiation	2.1	Radiation physics and detector fundamentals
	2.2	Detection systems
	2.3	Application, radiation generators, new technology
3 Optics and Photonics	3.1	Basic optics and frontier of optics
	3.2	Equipment optics and materials
	3.3	Information photonics and image engineering
	3.4	Biomedical optics
	3.5	Laser system and materials
	3.6	Ultrashort-pulse and high-intensity lasers
	3.7	Laser processing
	3.8	Optical measurement, instrumentation, and sensor
	3.9	Terahertz technologies
	3.10	Optical quantum physics and technologies
	3.11	Photonic structures and phenomena
	3.12	Nanoscale optical science and near-field optics
	3.13	Semiconductor optical devices
	3.14	Optical control devices and optical fibers
	3.15	Silicon photonics
4 JSAP-OSA Joint Symposia	4.1	Plasmonics
	4.2	Bio- and Medical Photonics
	4.3	Nano- and Micro-Photonics
	4.4	Opto-electronics
	4.5	Information Photonics
	4.6	Nanocarbon and 2D Materials
	4.7	Terahertz Photonics
	4.8	Strong Light Excitation Phenomena Applied to Materials and Bio Engneering
	4.9	Quantum Optics
6 Thin Films and Surfaces	6.1	Ferroelectric thin films
	6.2	Carbon-based thin films
	6.3	Oxide electronics
	6.4	Thin films and new materials
	6.5	Surface physics, vacuum
	6.6	Probe microscopy
7 Beam Technology and Nanofabrication	7.1	X-ray technologies
	7.2	Applications and technologies of electron beams
	7.3	Micro/Nano patterning and fabrication
	7.4	Buried interface sciences with quantum beam
	7.5	Ion beams
	7.6	Atomic/molecular beams and beam-related new technologies
8 Plasma Electronics *All-English session is scheduled in the section 8.8	8.1	Plasma production and control
	8.2	Plasma measurements and diagnostics
	8.3	Plasma deposition of thin film and surface treatment
	8.4	Plasma etching
	8.5	Plasma nanotechnology
	8.6	Plasma life sciences
	8.7	Plasma phenomena, emerging area of plasmas and their new applications
	8.8	Plasma Electronics English Session *All-English Session

Table 1. Regular Sessions (continued)

Category	Section	
9 Applied Materials Science	9.1	Dielectrics, ferroelectrics
	9.2	Nanowires and nanoparticles
	9.3	Nanoelectronics
	9.4	Thermoelectric conversion
	9.5	New functional materials and new phenomena
10 Spintronics and Magnetics *English presentations are welcomed in this category. Outstanding presentations by student speakers will be awarded by Professional Group of Spintronics.	10.1	Emerging materials in spintronics and magnetics (including fabrication and characterization methodologies)
	10.2	Fundamental and exploratory device technologies for spin
	10.3	Spin devices, magnetic memories and storages
	10.4	Semiconductor spintronics, superconductor, multiferroics
	10.5	Application of magnetic field
11 Superconductivity	11.1	Fundamental properties
	11.2	Thin and thick superconducting films, coated conductors and film crystal growth
	11.3	Critical current, superconducting power applications
	11.4	Analog applications and their related technologies
	11.5	Junction and circuit fabrication process, digital applications
12 Organic Molecules and Bioelectronics	12.1	Fabrications and structure controls
	12.2	Characterization and materials physics
	12.3	Functional materials and novel devices
	12.4	Organic light-emitting devices and organic transistors
	12.5	Organic solar cells
	12.6	Nanobiotechnology
	12.7	Biomedical engineering and biochips
13 Semiconductors *All-English session is scheduled in the section 13.6.	13.1	Fundamental properties, surface and interface, and simulations of Si related materials
	13.2	Exploratory materials, physical properties, devices
	13.3	Insulator technology
	13.4	Si wafer processing /Si based thin film /MEMS/Integration technology
	13.5	Semiconductor devices and related technologies
	13.6	Semiconductor English Session
	13.7	Nanostructures, quantum phenomena, and nano quantum devices
	13.8	Compound and power electron devices and process technology
	13.9	Optical properties and light-emitting devices
	13.10	Compound solar cells
15 Crystal Engineering	15.1	Bulk crystal growth
	15.2	II-VI and related compounds
	15.3	III-V-group epitaxial crystals/Fundamentals of epitaxy
	15.4	III-V-group nitride crystals
	15.5	Group IV crystals and alloys
	15.6	Group IV Compound Semiconductors (SiC)
	15.7	Crystal evaluation, impurities and crystal defects
16 Amorphous and Microcrystalline Materials	16.1	Fundamental properties, evaluation, process and devices in disordered materials
	16.2	Energy harvesting
	16.3	Bulk, thin-film and other silicon-based solar cells
17 Nanocarbon Technology	17.1	Carbon nanotubes & other nanocarbon materials
	17.2	Graphene
	17.3	Layered materials

Table 2. Joint Sessions

Joint Session K "Wide bandgap oxide semiconductor materials and devices"	21.1	Joint session of 6.3 Oxide-based electronics, 6.4 New thin film materials in 6. Thin Films and Surfaces and 15.2 II-VI-group crystals and multicomponent crystals in 15. Crystal Engineering.
Joint Session M "Phonon Engineering"	22.2	Joint session of 9.4 Thermoelectric conversion, 13.7 Nano structures and quantum phenomena and 17 Nanocarbon Technology.

Table 3. Symposium

Date	Related Category Symporsium Title
9/5 (Tue.)	1.Interdisciplinary Physics and Related Areas of Science and Technology Manpower Training for Science and Technology Educational Activities and Revitalization for the Kyushu Area
	3.Optics and Photonics Novel optical metrologies based on advanced photonics
	6.Thin Films and Surfaces Materials Nano-technology: Surfaces and Interfaces of Thin Films and Nano-composites
	12. Organic Molecules and Bioelectronics New developments on flexible energy harvesting devices
	13.Semiconductors Advances and future prospects of luminescent devices based on new material and quantum structure
	13.Semiconductors The history and future of Multinary Compounds and Solar Cells - 30th anniversary symposium of Professional Group of Multinary Compounds and Solar Cells -
	15.Crystal Engineering Science of impurity control in silicon wafers
9/6 (Wed.)	2.Ionizing Radiation International Linear Collider and Its Technology
	3.Optics and Photonics Electromagnetic controls in quantum hybrid systems
	6.Thin Films and Surfaces Oxide terahertz optical properties and devices
	6.Thin Films and Surfaces 13.Semiconductors Nanoscale 3D analyses for new device and materials development
	8.Plasma Electronics Plasma application for advanced agriculture: creation and control of novel environments for plant growth
	10.Spintronics and Magnetics Frontier of the studies weaved by light and spins
	15.Crystal Engineering Materials Science and Advanced Electronics Created by Singularity of Nitride Semiconductors ～Crystal Growth, Characterization and Application for Advanced GaN Electron Devices～
	17.Nanocarbon Technology Latest Application Researches and Future Prospects of Functional Atomic Layers
9/7 (Thu.)	12.Organic Molecules and Bioelectronics Organic Devices for Sensing to Next Generation of IoT
	12.Organic Molecules and Bioelectronics New Trend: Interdisciplinary approach to link biological materials and advanced device applications
	13.Semiconductors Challenges for'multi-scale' processing — dry, wet, or else?…
	13.Semiconductors Film Formation and Low Temperature of IV Element Semiconductor
	13.Semiconductors Recent GFIS･advanced ion source microscopy technologies and its future prospects for R & D of materials and devices
	15.Crystal Engineering Frontier of the research in dislocations
9/8 (金)	15.Crystal Engineering III-V semiconductor growth technology for innovative devices
	Joint Session K Gallium Oxide : Novel Wide Band-Gap Oxide Material for Future Generation

Submission Guidelines (for contributed papers)

1 Qualification

Speakers of contributed presentation (oral and poster presentations) should be JSAP Official Members, Student Members and JSAP's Partner Societies* Members.

*JSAP's partner societies: American Physical Society (APS), CSOE(Chinese Society for Optical Engineering), European Optical Society (EOS), European Physical Society (EPS), Institute of Physics (IOP), Korean Physical Society (KPS), Optical Society of America (OSA), Optical Society of Korea (OSK), Physics Education Society of Japan (PESJ), Physical Society of Republic of China (PSROC), Société Française de Physique (SFP), International Society for Optical Engineering (SPIE) and Taiwan Photonics Society (TPS).

2. Handling of abstract (PDF)

1) Our program committee draws up a program according to speakers' requests. However, the program committee may forward your abstract to another category for the benefit of the overall program.
2) JSAP holds the copyright on the submitted abstracts and all the submitted abstracts will be included in the abstracts DVD-ROM and uploaded on the online conference program.
3) The abstracts submitted to the JSAP-OSA Joint Symposia (held only in JSAP Autumn Meeting) will be published in OSA's Optics InfoBase. JSAP grants to OSA a perpetual, non-exclusive, royalty-free license to use them in any type of media including print or electronic.
4) The maximum number of submission per person is 3. If you wish to make 4 or more presentations, please submit a document explaining that there is no overlapping in the contents.
5) JSAP will not accept any abstracts that
   i) include contents that is not relevant to the field of applied physics (in a broad sense)
   ii) do not comply with this abstract submission guidelines
   iii) include contents that may damage our trust and dignity

3. JSAP Young Scientist Presentation Award

JSAP Young Scientist Presentation Award will be presented to young JSAP members (under 33 years of age as of April 1, 2018) who have presented outstanding papers .
To apply for the award, please select "apply" upon online submission. Applicants for the award will be indicated as such in the program.

4. Poster Awards

Poster Awards will be given to the outstanding posters. The nominees for Poster Awards will be selected by our program committee. No entry is required.
The authors of the nominated posters will be informed beforehand. The next screening will be done during the first 30 minutes of the session. The presenting authors of the nominated posters should be present in front of their posters during that time. Selection committee will vote and decide the final winner.